

Application No. 10/618,424  
Response to Office Action

Customer No. 01933

**Listing of Claims:**

Claims 1-6 (Canceled).

7. (Currently Amended) A semiconductor light-receiving module comprising:

a semiconductor light-receiving element; and  
an incident light direction device; [[,]]

5 wherein the semiconductor light-receiving element comprises:

a substrate;

a lower semiconductor layer formed on the substrate,  
and having a function as an optical waveguide;

10 a light absorbing layer formed on the lower semiconductor layer, and having a refractive index higher than that a refractive index of the lower semiconductor layer;

an upper cladding layer formed on the light absorbing layer, and having a refractive index lower than ~~that the~~ refractive index of the lower semiconductor layer;

15 a light incident facet ~~formed on so as to include~~ including at least one facet of the substrate, the lower semiconductor layer and the light absorbing layer; and

electrodes which output current generated by absorption of ~~the~~ light entering from the light incident facet in the light

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20 absorbing layer, by way of the upper cladding layer and the lower semiconductor layer; [[,]] and

wherein the incident light direction device ~~directs to~~  
~~irradiate positions the semiconductor light-receiving element~~  
~~such that the light is irradiated onto the light incident facet~~  
25 at a predetermined angle ~~from~~ with respect to the light incident  
facet of ~~the semiconductor light-receiving element, and thereby~~  
~~such that~~ a part of the light entering the light absorbing layer  
of ~~the semiconductor light-receiving element can propagate~~  
propagates in a ~~parallel~~ direction parallel to ~~the~~ a bottom face  
30 of the upper cladding layer in at least one of the light  
absorbing layer and the lower semiconductor layer, while another  
part of the light entering the light absorbing layer is reflected  
at the bottom face of the upper cladding layer and ~~can propagate~~  
propagates in an oblique direction in the light absorbing layer  
35 and the lower semiconductor layer.

8. (Currently Amended) The semiconductor light-receiving module according to claim 7, wherein an angle formed between the light incident facet and ~~the~~ a bottom face of the light absorbing layer of ~~the semiconductor light-receiving element is set at~~ 90 degrees.

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9. (Currently Amended) The semiconductor light-receiving module according to claim 7, wherein an angle formed between the light incident facet and the a bottom face of the light absorbing layer ~~of the semiconductor light receiving element~~ is set at less  
5 than 90 degrees, and ~~at an angle~~ is determined by a crystal azimuth of a material ~~for composing from which~~ the light incident facet is formed.

10. (Currently Amended) The semiconductor light-receiving module according to claim 7, wherein an angle formed between the light incident facet and the a bottom face of the light absorbing layer ~~of the semiconductor light receiving element~~ is set at less  
5 than 90 degrees, and ~~at an angle~~ is larger than the an angle determined by a crystal azimuth of a material ~~for composing from which~~ the light incident facet is formed.

11. (Currently Amended) The semiconductor light-receiving module according to claim 7, wherein the lower semiconductor layer ~~of the semiconductor light receiving element~~ is made of a semiconductor material of quaternary composition.

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12. (Currently Amended) The semiconductor light-receiving module according to claim 7, wherein the lower semiconductor layer ~~is composed of~~ comprises a combination of ~~a~~ at least one high-refractive-index layer and ~~a~~ at least one

5 low-refractive-index layer such that an effective index of the lower semiconductor layer ~~becomes~~ is higher than ~~a~~ the refractive index of the upper cladding layer, for the light entering the light incident facet ~~of the semiconductor light-receiving element~~.

13. (Currently Amended) The semiconductor light-receiving module according to claim 7, wherein the lower semiconductor layer ~~of the semiconductor light-receiving element~~ is made of an n-type semiconductor material, and the upper cladding layer is made of a p-type semiconductor material.

14. (Currently Amended) The semiconductor light-receiving module according to claim 7, wherein the lower semiconductor layer ~~of the semiconductor light-receiving element~~ is made of a p-type semiconductor material, and the upper cladding layer is made of an n-type semiconductor material.

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15. (Currently Amended) The semiconductor light-receiving module according to claim 7, wherein the light entering the light incident facet is irradiated to the light absorbing layer through at least the lower semiconductor layer, by adjusting at least one  
5 of ~~the~~ an incident position and an incident angle of the light with respect to the light incident facet ~~of the semiconductor light-receiving element~~.

Claims 16-25 (Canceled).